

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1764942	display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 10:56
L2	66112	(EL (electroluminescent)) & display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 10:56
L3	6446	2 & (transistor\$1 with (driv\$3 current))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:15
L4	879	3 & (idd (light\$3 near3 dop\$3 near3 drain\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:45
L5	109	4 & ((transistor\$1 with (driv\$3 current)) with (p near7 (chanel type)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:16
L6	71	5 & (transistor\$1 with (switch\$3 select\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:17
L7	0	6 & baron & concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:07
L8	33	6 & boron & concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:18

L9	19	8 & (p with concentration with boron)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:08
L10	8169	2 & ((tft\$1 transistor\$1) with (driv\$3 current))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:16
L11	1483	10 & (ldd (light\$3 near3 dop\$3 near3 drain\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:16
L12	109	11 & ((transistor\$1 with (driv\$3 current)) with (p near7 (chanel type)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:16
L13	71	12 & (transistor\$1 with (switch\$3 select\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:17
L14	87	12 & ((tft\$1 transistor\$1) with (switch\$3 select\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 11:17
L15	47	14 & boron & concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:47
L16	47	15 & (gate near5 electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 12:14

L17	39	16 & (concentration with (low & high))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:46
L18	36	17 & ((p near7 (chanel type)) with (high concentration))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 12:16
L19	18	17 & ((p near7 (chanel type)) with (high near5 concentration))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 12:17
L20	4	19 & ((n near7 (chanel type)) with (low near5 concentration))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:15
L21	2	"20040217355"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:16
L22	2	21 & gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:19
L23	1	22 & electrode\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:40
L24	1407	((driv\$3 current) near5 (transistor\$1 tft\$1)) near9 ((form\$3 compris\$3) near9 (p near5 (chanel type)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:04

L25	329	2 & 24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:45
L26	219	25 & (ldd (light\$3 near3 dop\$3 near3 drain\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:45
L27	141	26 & (concentration with (low & high))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:46
L28	134	27 & boron & concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:50
L29	104	28 & (((transistor tft) near7 (select\$3 switch\$3)) with pixel\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 13:52
L30	1179	((driv\$3 current) near5 (transistor\$1 tft\$1)) near9 (ldd (light\$3 near3 dop\$3 near3 drain\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 14:05
L31	84	29 & 30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:03
L32	630	((driv\$3 current) near3 (transistor\$1 tft\$1)) near9 (((form\$3 compris\$3) near3 (p near5 (chanel type)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:07

L33	20	((driv\$3 current) near3 (transistor\$1 tft\$1)) near9 ((form\$3 compris\$3) near3 (p near5 (chanel type)))) with (ldd (light near3 dop\$3 near3 drain\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:19
L34	5	2 & 33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:18
L35	158	2 & 32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:18
L36	113	35 & (ldd (light near3 dop\$3 near3 drain\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:20
L37	109	36 & ((transistor\$1 tft\$1) near5 (form\$3 compris\$3) near9 (p nept chanel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:22
L38	0	36 & ((transistor\$1 tft\$1) near5 (form\$3 compris\$3) near9 (p near7 chanel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:22
L39	109	36 & ((transistor\$1 tft\$1) near5 (form\$3 compris\$3) near9 (p near7 (type channel)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:24
L40	79	36 & ((transistor\$1 tft\$1) near5 (form\$3 compris\$3) near9 (ldd (light near3 dop\$3 near3 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:25

L41	79	39 & ((transistor\$1 tft\$1) near5 (form\$3 compris\$3) near9 (ldd (light near3 dop\$3 near3 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:27
L42	68	41 & ((transistor\$1 tft\$1) near7 (select\$3 switch\$3) with pixel\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:38
L43	8	42 & (p near5 ((low & high) near3 concentration))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/14 15:39